

BAS321

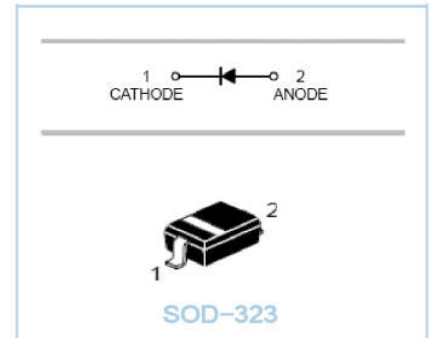
Silicon Epitaxial Planar Diode

FEATURES

- Fast Switching Speed.
- Surface Mount Package Ideally Suited For Automatic Insertion
- For General Purpose Switching Applications
- High Conductance

APPLICATIONS

- Surface mount fast switching diode



ORDERING INFORMATION

Type No.	Marking	Package Code
BAS321	A7	SOD-323

MAXIMUM RATING @ Ta=25°C unless otherwise specified

Characteristic	Symbol	TECHNICAL DATA	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	250	V
Working Peak Reverse Voltage	V_{RWM}	200	V
DC Reverse Voltage	V_R		
RMS Reverse Voltage	$V_{R(RMS)}$	141	V
Forward Continuous Current	I_{FM}	400	mA
Average Rectified Output Current	I_o	200	mA
Non-Repetitive Peak Forward Surge Current @t=1.0 μ s @t=1.0 s	I_{FSM}	2.5 0.5	A
Repetitive Peak Forward Surge Current	I_{FRM}	625	mA
Power Dissipation	P_d	200	mW
Thermal Resistance Junction to Ambient Air	$R_{\theta JA}$	625	°C/W
Operating and Storage Temperature Range	T_j, T_{STG}	-65 to +150	°C

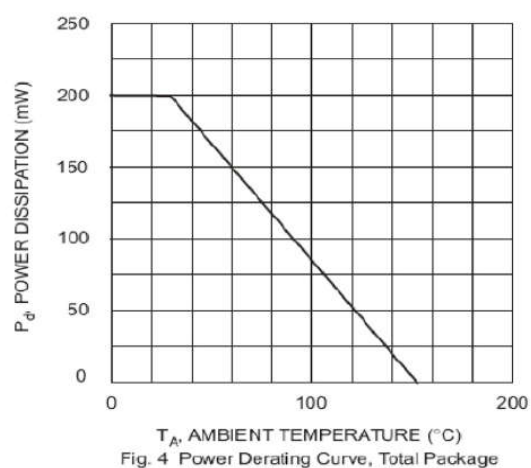
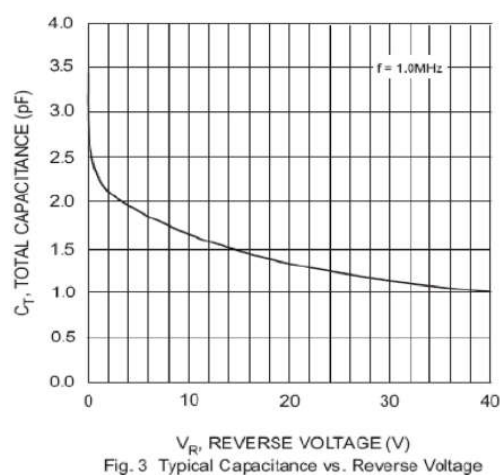
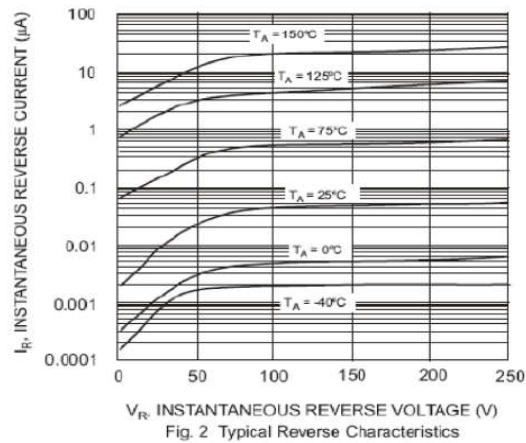
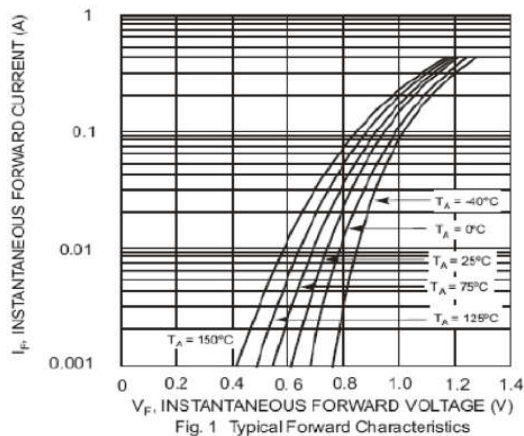


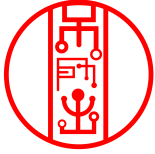
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ELECTRICAL CHARACTERISTICS @ $T_a=25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
Forward Voltage	V_{FM}	-	1.0 1.25	V	$I_F=100\text{mA}$ $I_F=200\text{mA}$
Reverse Current	I_R	-	0.1	mA	$V_R=200\text{V}$
Capacitance between terminals	C_T	-	5	pF	$V_R=0, f=1.0\text{MHz}$
Reverse Recovery Time	t_{rr}	-	50	ns	$I_F=I_R=30\text{mA}$, $I_{rr}=0.1 \times I_R, R_L=100\Omega$

TYPICAL CHARACTERISTICS @ $T_a=25^\circ\text{C}$ unless otherwise specified



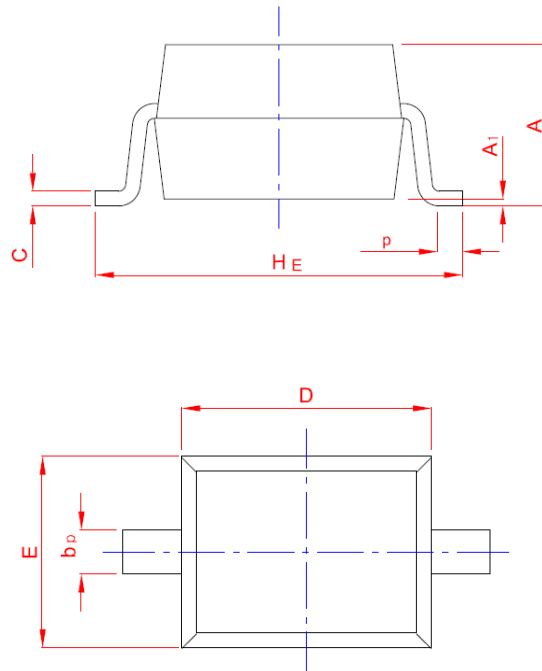


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PACKAGE OUTLINE

Plastic surface mounted package;

2 leads



UNIT	A	bp	C	D	E	HE	A1	Lp
mm	1.20 0.90	0.40 0.25	0.15 0.10	1.80 1.60	1.35 1.15	2.80 2.30	0.10 0.01	0.50 0.20